

GSD3004N1F

Switching Diode

Product Description

Switching Diode 350V and 225mA

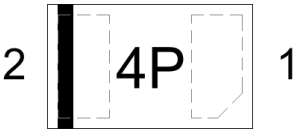
Features

- Fast Switching Speed.
- Low Reverse Leakage Current

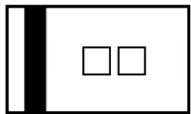
Mechanical Data

- DFN1006-2L Package
- Epoxy Meets UL 94 V-0 Flammability Rating
- RoHS Compliant and Halogen Free

Packages & Pin Assignments

DFN1006-2L	Equivalent Circuit
 <p>*Band indicates Cathode</p>	

Ordering and Marking Information

Ordering Information			
Part Number	Package	Marking Code	Quantity/Reel
GSD3004N1F	DFN1006-2L	4P	10,000 PCS
GSD3004N1F			
- Product Code: GSD3004	- Package Code: N1 for DFN1006-2L Package	- Green Level: F for RoHS Compliant and Halogen Free	
Marking Information			
	- Product Code: □□ is 4P *Band for Cathode Side		

GSD3004N1F

Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Symbol	Parameter	Value	Units
V _{RRM}	Peak Repetitive Reverse Voltage	350	V
V _{RM}	Peak Non-Repetitive Reverse Voltage	300	V
V _{R(RMS)}	RMS Reverse Voltage	212	V
I _{FM}	Forward Continuous Current	225	mA
I _{FSM}	Repetitive Peak Forward Current	625	mA
I _{FSM}	Non-Repetitive Peak Forward Surge Current (@t=1.0 us)	4	A
P _D	Power Dissipation	250	mW
R _{θJA}	Thermal Resistance from Junction to Ambient	500	°C/W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-55 to +150	°C

These ratings are limiting values above which the serviceability of the diode may be impaired.

Electrical Characteristics (T_A=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min	Max	Units
V _R	Reverse Breakdown Voltage	I _R =150μA	350		V
V _F	Forward Voltage	I _F =20mA		0.87	V
		I _F =100mA		1.00	V
		I _F =200mA		1.25	V
I _R	Reverse Current	V _R = 240V (25°C)		100	nA
		V _R = 240V (150°C)		100	uA
C _T	Capacitance	V _R = 0V, f = 1MHz		5	pF
t _{rr}	Reverse Recovery Time	I _F = I _R =30mA, I _{RR} = 0.1x I _R R _L = 100Ω		50	ns

Typical Characteristics

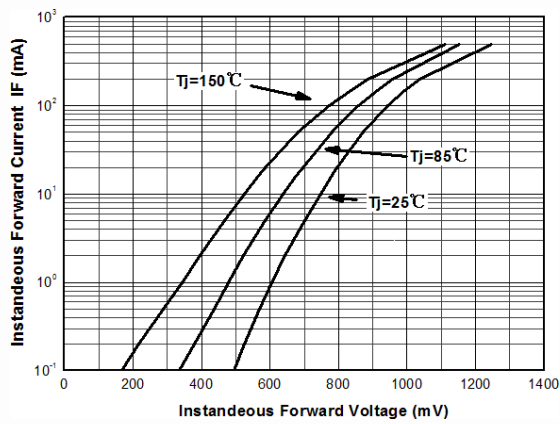


Fig. 1 Forward Characteristics

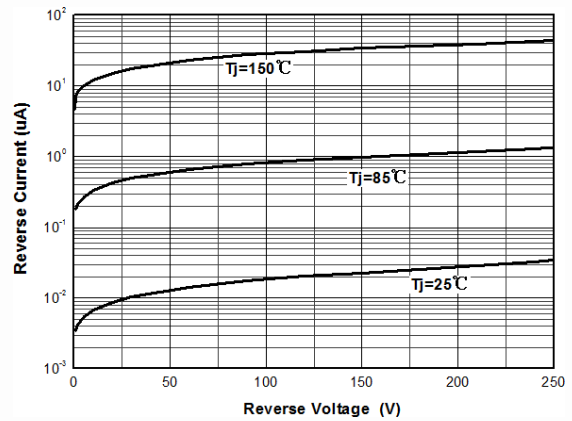


Fig. 2 Reverse Characteristics

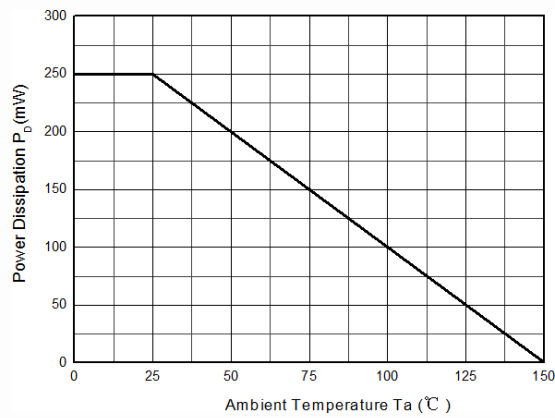
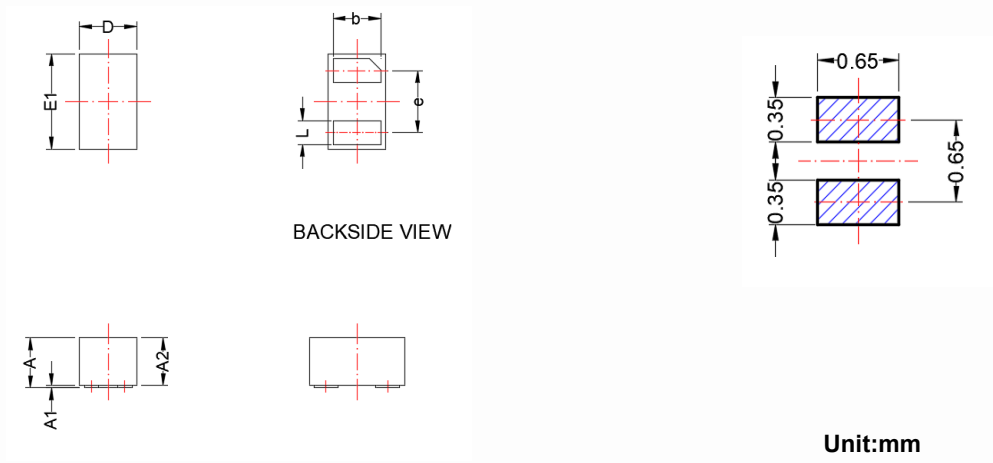


Fig. 3 Power Derating Curve

DFN1006-2L

Package Dimension

Recommended Land Pattern



Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	0.45	0.60	0.018	0.024
A1	0.00	0.05	0.000	0.002
A2	0.40	0.60	0.016	0.024
b	0.45	0.55	0.018	0.022
D	0.55	0.65	0.022	0.026
E1	0.95	1.05	0.037	0.041
e1	0.65 BSC		0.026 BSC	
L	0.20	0.30	0.008	0.012





NOTE:



Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.

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